MUR180E, MUR1100E

MUR1100E is a Preferred Device

SWITCHMODE™ Power Rectifiers

Ultrafast “E” Series with High Reverse Energy Capability

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state–of–the–art devices have the following features:

- 10 mjoules Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 Volts

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 0.4 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16″ from case
- Shipped in plastic bags, 1000 per bag
- Available Tape and Reeled, 5000 per reel, by adding a “RL” suffix to the part number
- Polarity: Cathode Indicated by Polarity Band
- Marking: MUR180E, MUR1100E

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage MUR180E	V_R	800	
MUR1100E		1000	
Average Rectified Forward Current (Note 1.) (Square Wave Mounting Method #3 Per Note 3.)	$I_{F(AV)}$	1.0 @ $T_A = 95°C$	A
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	35	A
Operating Junction Temperature and Storage Temperature Range	T_J, T_{stg}	–65 to +175	°C

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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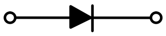
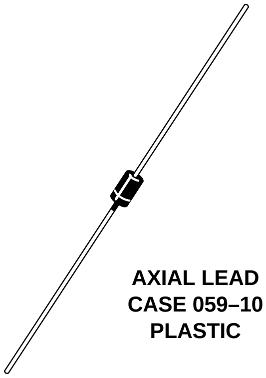
http://onsemi.com

ULTRAFAST
RECTIFIERS
1.0 AMPERES
800–1000 VOLTS





AXIAL LEAD
CASE 059–10
PLASTIC

MARKING DIAGRAM

MUR1x0E = Device Code
x = 8 or 10

ORDERING INFORMATION

Device	Package	Shipping
MUR180E	Axial Lead	1000 Units/Bag
MUR180ERL	Axial Lead	5000/Tape & Reel
MUR1100E	Axial Lead	1000 Units/Bag
MUR1100ERL	Axial Lead	5000/Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	See Note 3.	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 2.) (i_F = 1.0 Amp, T_J = 150°C) (i_F = 1.0 Amp, T_J = 25°C)	v_F	 1.50 1.75	Volts
Maximum Instantaneous Reverse Current (Note 2.) (Rated dc Voltage, T_J = 100°C) (Rated dc Voltage, T_J = 25°C)	i_R	 600 10	μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs) (I_F = 0.5 Amp, i_R = 1.0 Amp, I_{REC} = 0.25 Amp)	t_{rr}	 100 75	ns
Maximum Forward Recovery Time (I_F = 1.0 Amp, di/dt = 100 Amp/μs, Recovery to 1.0 V)	t_{fr}	75	ns
Controlled Avalanche Energy (See Test Circuit in Figure 6)	W_{AVAL}	10	mJ

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

ELECTRICAL CHARACTERISTICS

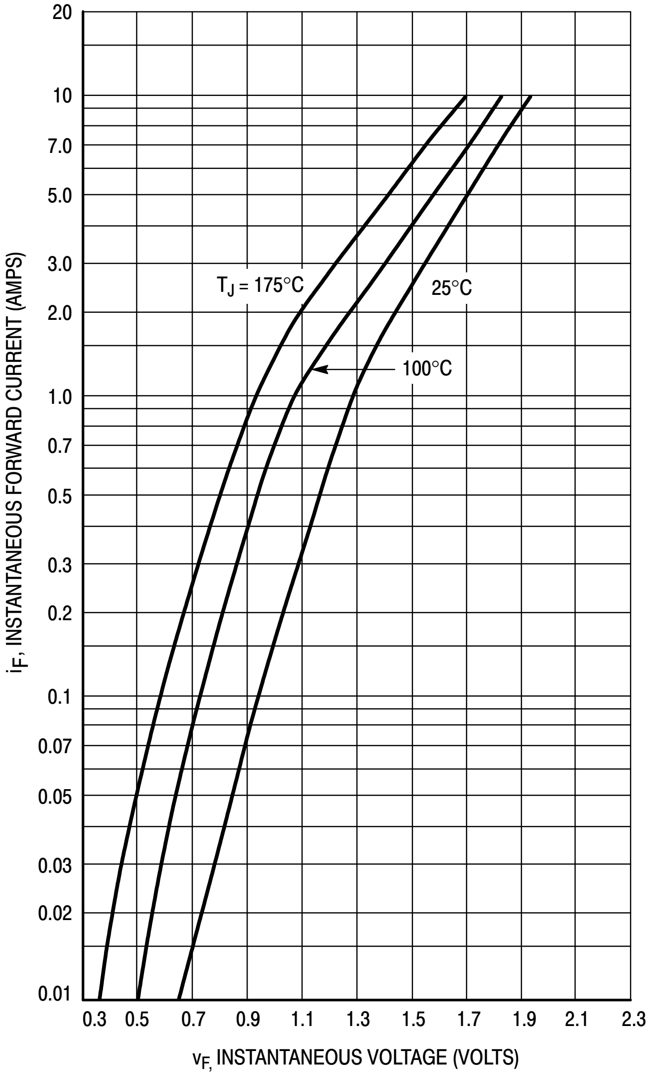


Figure 1. Typical Forward Voltage

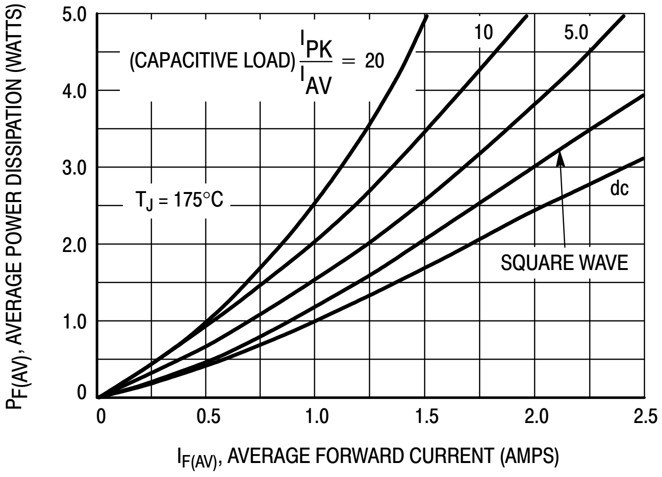


Figure 4. Power Dissipation

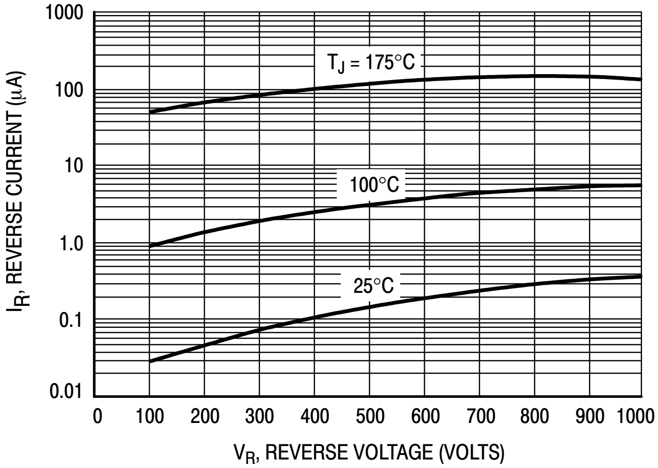


Figure 2. Typical Reverse Current*

* The curves shown are typical for the highest voltage device in the grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

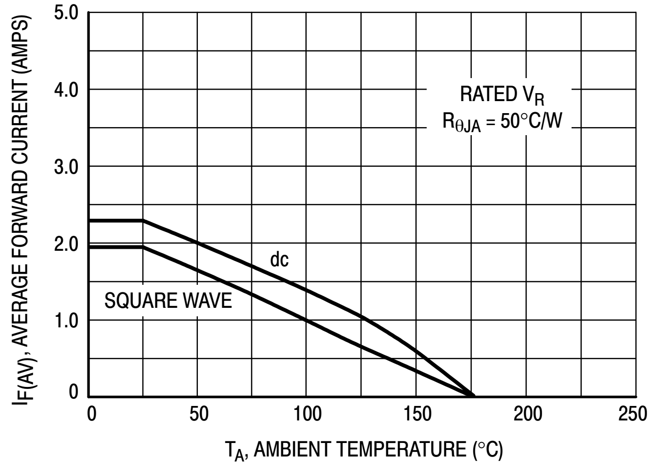


Figure 3. Current Derating (Mounting Method #3 Per Note 1)

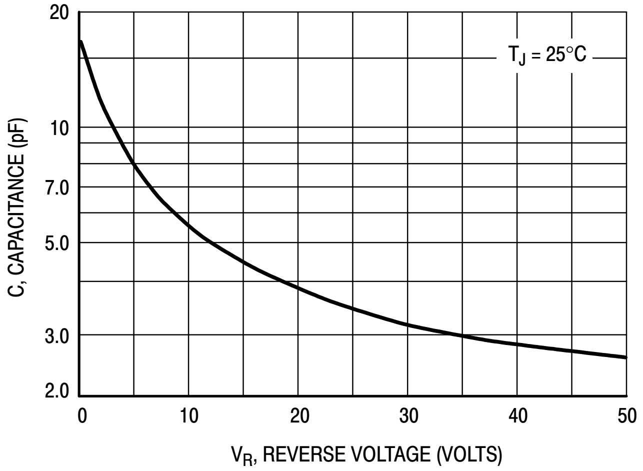


Figure 5. Typical Capacitance

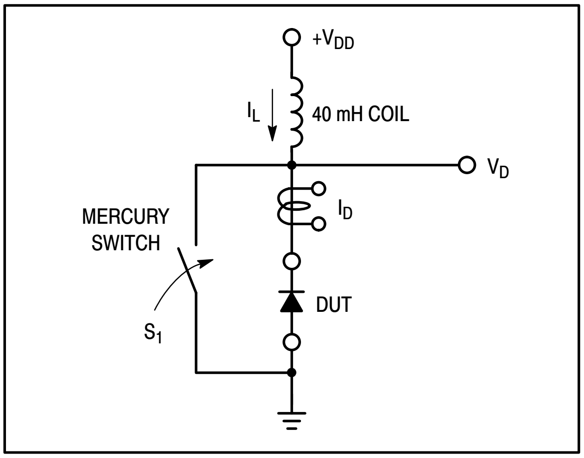


Figure 6. Test Circuit

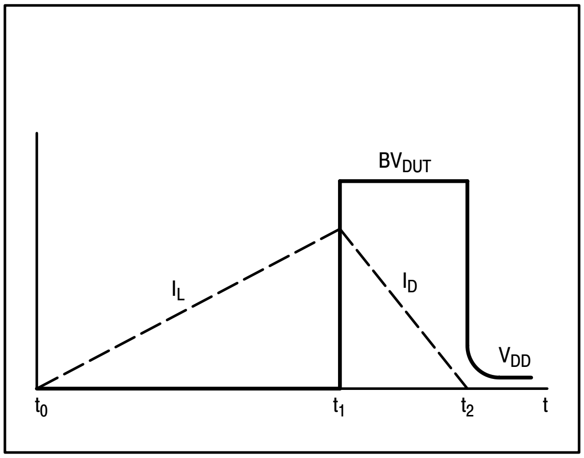


Figure 7. Current–Voltage Waveforms

The unclamped inductive switching circuit shown in Figure 6 was used to demonstrate the controlled avalanche capability of the new “E’’ series Ultrafast rectifiers. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2.

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

The oscilloscope picture in Figure 8, shows the information obtained for the MUR8100E (similar die construction as the MUR1100E Series) in this test circuit conducting a peak current of one ampere at a breakdown voltage of 1300 volts, and using Equation (2) the energy absorbed by the MUR8100E is approximately 20 mjoules.

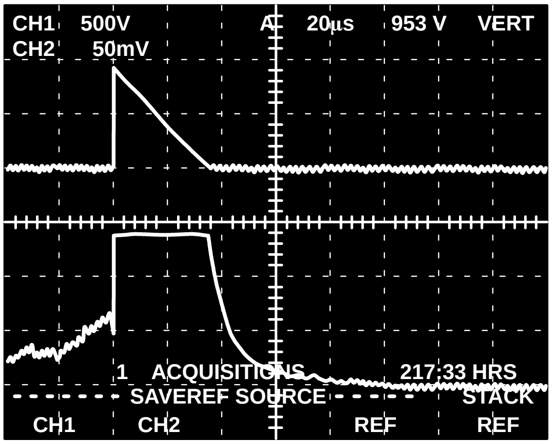
Although it is not recommended to design for this condition, the new “E’’ series provides added protection against those unforeseen transient viruses that can produce unexplained random failures in unfriendly environments.

EQUATION (1):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^{2} \left(\frac{BV_{DUT}}{BV_{DUT} - V_{DD}} \right)$$

EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^{2}$$



CHANNEL 2:
I_L
0.5 AMPS/DIV.

CHANNEL 1:
V_{DUT}
500 VOLTS/DIV.

TIME BASE:
20 µs/DIV.

Figure 8. Current–Voltage Waveforms

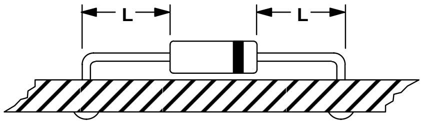
NOTE 3. — AMBIENT MOUNTING DATA

Data shown for thermal resistance junction to ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

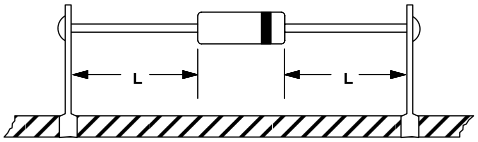
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

Mounting Method		Lead Length, L			Units
		1/8	1/4	1/2	
1	$R_{\theta JA}$	52	65	72	°C/W
2		67	80	87	°C/W
3		50			°C/W

MOUNTING METHOD 1

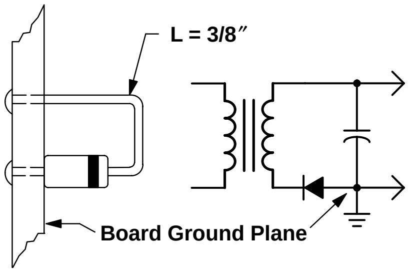


MOUNTING METHOD 2



Vector Pin Mounting

MOUNTING METHOD 3



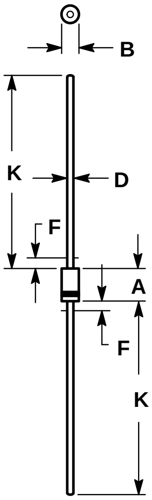
P.C. Board with
1–1/2″ X 1–1/2″ Copper Surface

PACKAGE DIMENSIONS

MINI MOSORB

CASE 59–10

ISSUE S



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 59−04 OBSOLETE, NEW STANDARD 59−09.
4. 59−03 OBSOLETE, NEW STANDARD 59−10.
5. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO−41 OUTLINE SHALL APPLY
6. POLARITY DENOTED BY CATHODE BAND.
7. LEAD DIAMETER NOT CONTROLLED WITHIN F DIMENSION.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.161	0.205	4.10	5.20
B	0.079	0.106	2.00	2.70
D	0.028	0.034	0.71	0.86
F	---	0.050	---	1.27
K	1.000	---	25.40	---

Notes

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